



Product Summary

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	I_D
68V	2.3m Ω @10V	130A

Feature

- Split Gate Trench Technology
- Low $R_{DS(ON)}$
- Low Gate Charge
- Low Gate Resistance
- 100% UIS Tested
- 100% ΔV_{DS} Tested

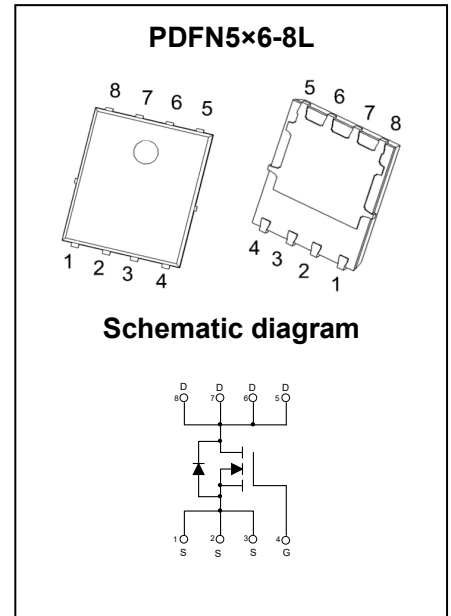
Application

- DC/DC Converter
- Synchronous Rectification
- High-Frequency Switch

MARKING:



T030N06L = Device Code
XX = Date Code
Solid Dot = Green Indicator



ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain - Source Voltage	V_{DS}	68	V
Gate - Source Voltage	V_{GS}	± 20	V
Continuous Drain Current ¹	I_D	130	A
Pulsed Drain Current ²	I_{DM}	520	A
Single Pulsed Avalanche Current ³	I_{AS}	35	A
Single Pulsed Avalanche Energy ³	E_{AS}	306	mJ
Power Dissipation ⁵	P_D	156	W
Thermal Resistance from Junction to Ambient ⁶	$R_{\theta JA}$	50	$^\circ\text{C}/\text{W}$
Thermal Resistance from Junction to Case	$R_{\theta JC}$	0.8	$^\circ\text{C}/\text{W}$
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature	T_{STG}	-55~ +150	$^\circ\text{C}$

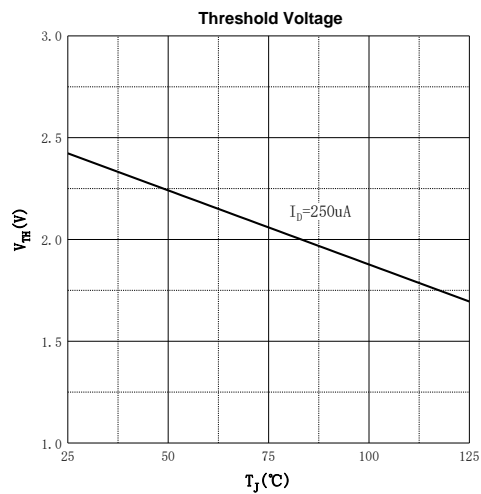
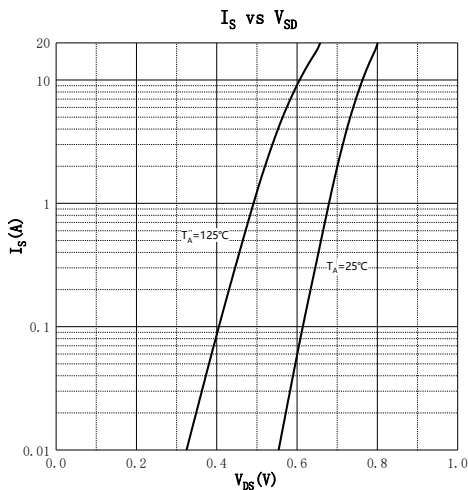
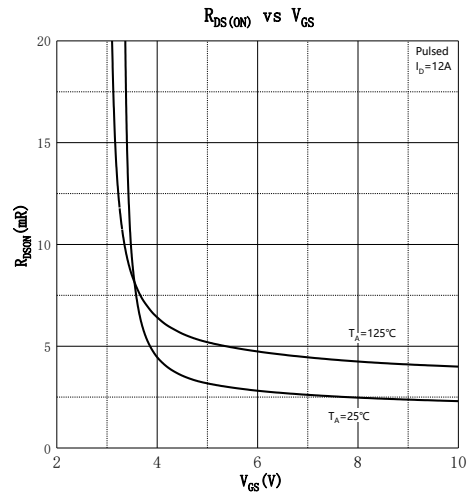
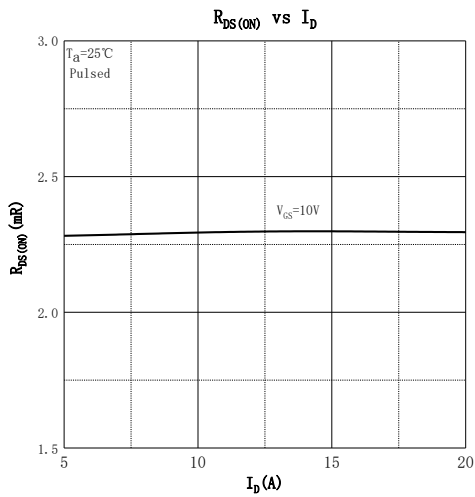
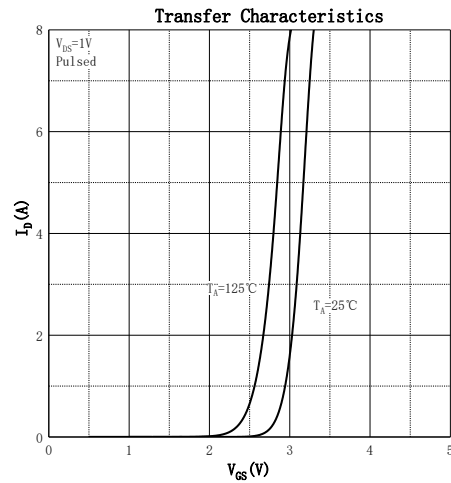
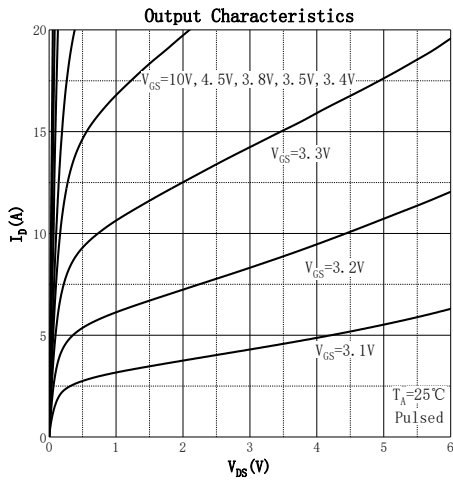
MOSFET ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

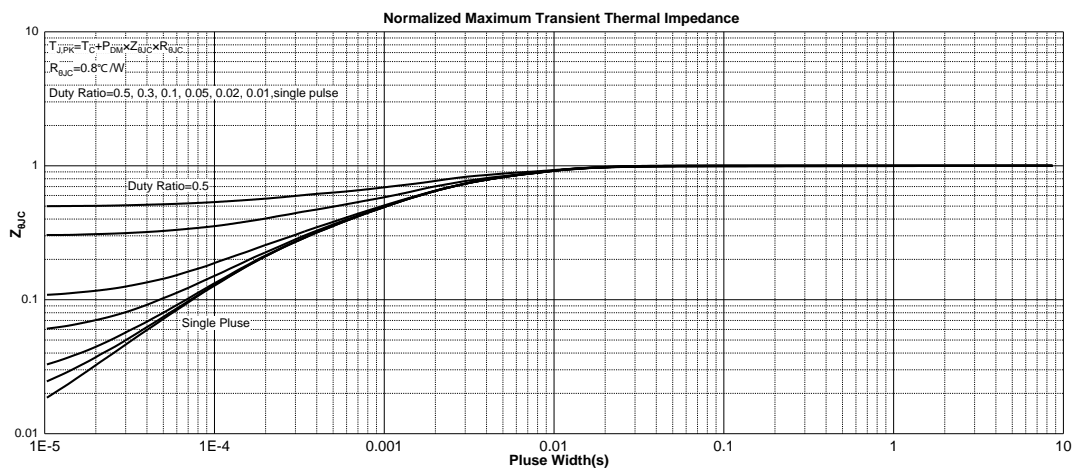
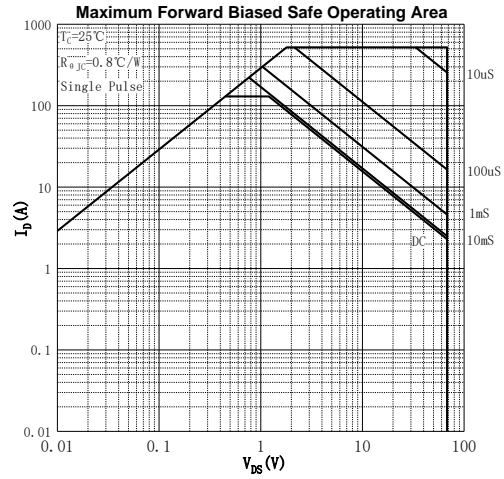
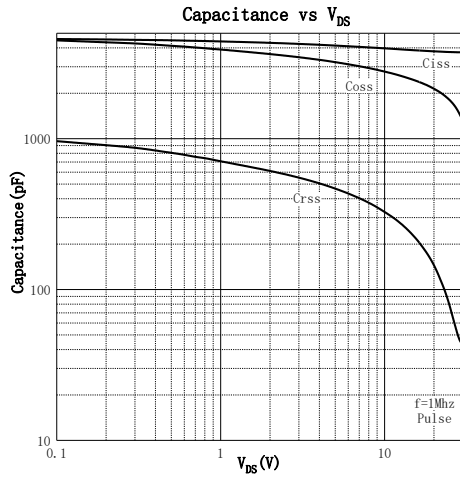
Parameter	Symbol	Test Condition	Min	Type	Max	Unit
Off Characteristics						
Drain - Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	68			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 60V, V_{GS} = 0V$			1	μA
Gate - Body Leakage Current	I_{GSS}	$V_{GS} = \pm 20V, V_{DS} = 0V$			± 100	nA
On Characteristics⁴						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	1	2.4	3	V
Drain-source On-resistance	$R_{DS(on)}$	$V_{GS} = 10V, I_D = 12A$		2.3	3	m Ω
Forward Transconductance	g_{FS}	$V_{DS} = 5V, I_D = 10A$		30		S
Dynamic Characteristics						
Input Capacitance	C_{iss}	$V_{DS} = 30V, V_{GS} = 0V, f = 1MHz$		3788		pF
Output Capacitance	C_{oss}			1075		
Reverse Transfer Capacitance	C_{rss}			46		
Gate Resistance	R_g	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$		2		Ω
Switching Characteristics						
Total Gate Charge	Q_g	$V_{DS} = 30V, V_{GS} = 10V, I_D = 20A$		50		nC
Gate-source Charge	Q_{gs}			12		
Gate-drain Charge	Q_{gd}			14		
Turn-on Delay Time	$t_{d(on)}$	$V_{DD} = 30V, V_{GS} = 10V, R_L = 1.5\Omega$ $R_G = 3\Omega$		20		ns
Turn-on Rise Time	t_r			6.5		
Turn-off Delay Time	$t_{d(off)}$			62		
Turn-off Fall Time	t_f			24		
Source - Drain Diode Characteristics						
Diode Forward Voltage ⁴	V_{SD}	$V_{GS} = 0V, I_S = 12A$			1.2	V

Notes :

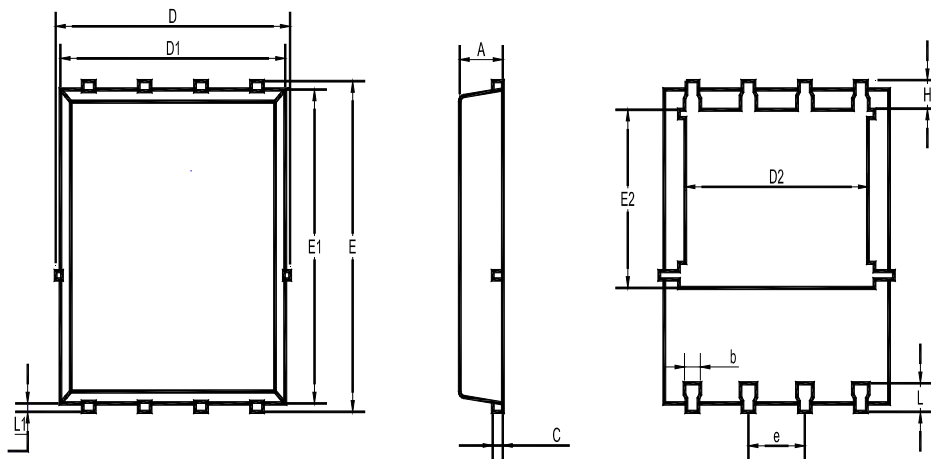
- 1.The maximum current rating is limited by package.And device mounted on a large heatsink
- 2.Pulse Test : Pulse Width $\leq 10\mu s$, duty cycle $\leq 1\%$.
- 3.EAS condition: $V_{DD} = 30V, V_{GS} = 10V, L = 0.5mH, R_G = 25\Omega$ Starting $T_J = 25^\circ\text{C}$.
- 4.Pulse Test : Pulse Width $\leq 300\mu s$, duty cycle $\leq 2\%$.
- 5.The power dissipation P_D is limited by $T_{J(MAX)} = 150^\circ\text{C}$.And device mounted on a large heatsink
- 6.Device mounted on $1in^2$ FR-4 board with 2oz. Copper, in a still air environment with $T_A = 25^\circ\text{C}$.

Typical Characteristics



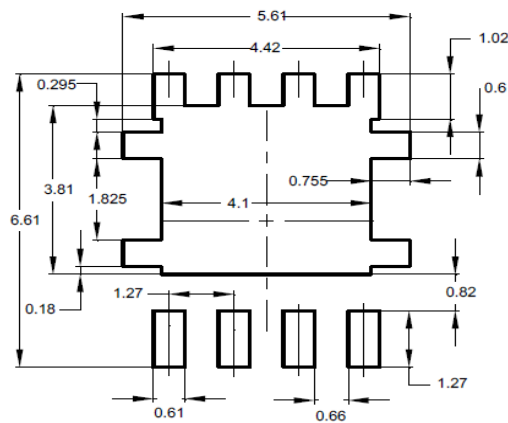


PDFN5×6-8L Package Information



UNIT	A	b	C	D	D1	D2	E	E1	E2	e	L	L1	H
mm	1.12	0.51	0.34	5.26	5.1	4.5	6.25	6	3.66	1.37	0.71	0.2	0.71
	0.9	0.33	0.11	4.7	4.7	3.56	5.75	5.6	3.18	1.17	0.35	0.06	0.35

Recommended Soldering Footprint



单击下面可查看定价，库存，交付和生命周期等信息

[>>GP\(格瑞宝\)](#)